

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

10/799,318

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
/M.P./	1A	4,887,255	12/12/1989	Handa, et al.	
	1B	5,744,864	04/28/1998	Cillessen, et al.	
	1C	6,225,655	05/01/2001	Moise, et al.	
	1D	6,255,130	07/03/2001	Kim	
	1E	6,362,499	03/26/2002	Moise, et al.	
	1F	6,563,174	05/13/2003	Kawasaki, et al.	
	1G	2003/0013261	01/16/2003	Asano	
	1H	2002/0153587	10/24/2002	Adkisson, et al.	
	1I	2003/0207502	11/06/2003	Yamazaki, et al.	
	1J	2003/0218221	11/27/2003	Wager, III, et al.	
/M.P./	1K	2003/0218222	11/27/2003	Wager, III, et al.	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
/M.P./	1L	WO 97/06544	02/20/1997	Cillessen, et al.		
/M.P./	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
/M.P./	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
/M.P./	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

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/M.P./	2A	2003/0219530	11/27/2003	Yamazaki, et al.	
	2B	2003/0111663	06/19/2003	Yagi	
	2C	2003/0047785	03/13/2003	Kawasaki, et al.	
	2D	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
	2E	10/763,353	01/23/2004		Semiconductor Device
/M.P./	2F	10/763,354	01/23/2004		Transistor including a Deposited Channel Region Having a ...
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/M.P./	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527. unknown date
/M.P./	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
/M.P./	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

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/M.P./	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
/M.P./	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
/M.P./	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

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/M.P./	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
/M.P./	4R	Pallecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
/M.P./	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

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/M.P./	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
/M.P./	5R	Uneno, K., et al. "Field-effect transistor on SrTiO <sub>3</sub> with sputtered Al <sub>2</sub> O <sub>3</sub> gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
/M.P./	5S	Wöllenstein, Jürgen, et al., "An insulated gate thin-film transistor using SnO <sub>2</sub> as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

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/M.P./	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO <sub>3</sub> Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
/M.P./	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
/M.P./	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLED's" Research Disclosure, p. 890 (July 1998).

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/Marcos Pizarro Crespo/

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08/10/2007